

Abstract of the Disclosure

A method of forming a conductive pattern of a semiconductor device includes forming a conductive layer on a substrate, forming a polishing protection layer on the substrate including over the conductive layer, and forming a step compensation layer on the polishing protection layer to reduce the step presented by the layer that is the polishing protection layer. The conductive layer is exposed by removing select portions of the step compensation layer and the polishing protection layer. The conductive pattern is ultimately formed on the substrate by etching the exposed conductive layer. By planarization the intermediate structure several times once the step compensation layer is formed, a highly uniform conductive layer is sure to be formed.